



STU312D

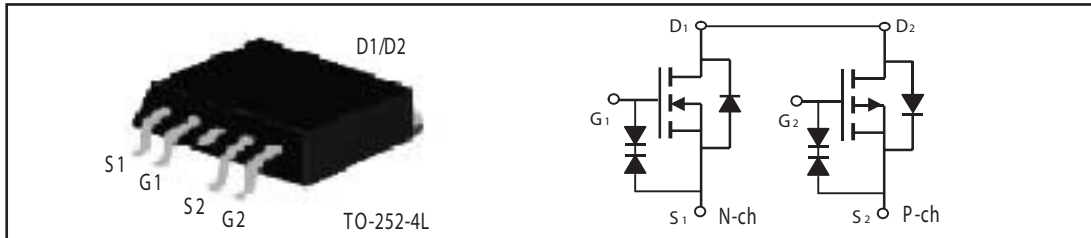
SamHop Microelectronics Corp.

Oct 08 2008

Dual Enhancement Mode Field Effect Transistor (N and P Channel)

PRODUCT SUMMARY (N-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
30V	18A	24 @ V _{GS} = 10V
		36 @ V _{GS} = 4.5V

PRODUCT SUMMARY (P-Channel)		
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-30V	-14A	34 @ V _{GS} = -10V
		54 @ V _{GS} = -4.5V



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V _{DS}	30	-30	V
Gate-Source Voltage	V _{GS}	±24	±24	V
Drain Current-Continuous @ T _c	I _D	18	-14	A
		15	-12	A
-Pulsed ^a	I _{DM}	50	-50	A
Drain-Source Diode Forward Current	I _S	10	-6	A
Maximum Power Dissipation	P _D	11		W
		7.7		
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 175		°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	13.6	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	120	°C/W

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N-Channel ELECTRICAL CHARACTERISTICS (T_A = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250uA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±24V, V _{DS} = 0V			±100	uA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250uA	1	1.8	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 10A		18	24	m ohm
		V _{GS} = 4.5V, I _D = 8A		24	36	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 4.5V	20			A
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 10A		15		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz		640		pF
Output Capacitance	C _{OSS}			180		pF
Reverse Transfer Capacitance	C _{RSS}			110		pF
Gate resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz		0.5		ohm
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 15V I _D = 1 A V _{GS} = 10V R _{GEN} = 6 ohm		13		ns
Rise Time	t _r			12		ns
Turn-Off Delay Time	t _{D(OFF)}			40		ns
Fall Time	t _f			7		ns
Total Gate Charge	Q _g	V _{DS} = 15V, I _D = 20A, V _{GS} = 10V		13		nC
		V _{DS} = 15V, I _D = 20A, V _{GS} = 4.5V		6.8		nC
Gate-Source Charge	Q _{gs}	V _{DS} = 15V, I _D = 20 A		1.5		nC
Gate-Drain Charge	Q _{gd}	V _{GS} = 10V		3.5		nC

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P-Channel ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -24V, V _{GS} = 0V			-1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±24V, V _{DS} = 0V			±100	uA
ON CHARACTERISTICS^a						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250uA	-1	-1.7	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -6A		27	34	m ohm
		V _{GS} = -4.5V, I _D = -4A		39	54	m ohm
On-State Drain Current	I _{D(ON)}	V _{DS} = -5V, V _{GS} = -10V	-20			A
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -6A		10		S
DYNAMIC CHARACTERISTICS^b						
Input Capacitance	C _{ISS}	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz		800		pF
Output Capacitance	C _{OSS}			215		pF
Reverse Transfer Capacitance	C _{RSS}			120		pF
Gate resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1.0MHz		4		ohm
SWITCHING CHARACTERISTICS^b						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = -15V I _D = -1A V _{GS} = -10V R _{GEN} = 6 ohm		12		ns
Rise Time	t _r			18		ns
Turn-Off Delay Time	t _{D(OFF)}			68		ns
Fall Time	t _f			38		ns
Total Gate Charge	Q _g	V _{DS} = -15V, I _D = -20A, V _{GS} = -10V		15		nC
		V _{DS} = -15V, I _D = -20A, V _{GS} = -4.5V		7		nC
Gate-Source Charge	Q _{gs}	V _{DS} = -15V, I _D = -20 A		1.3		nC
Gate-Drain Charge	Q _{gd}	V _{GS} = -10V		5		nC

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ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_s = 10A$	N-Ch	0.9	1.3	V
		$V_{GS} = 0V, I_s = -6A$	P-Ch	-0.9	-1.3	

Notes

a. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

N-Channel

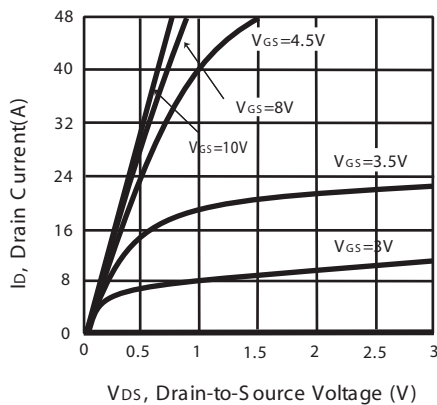


Figure 1. Output Characteristics

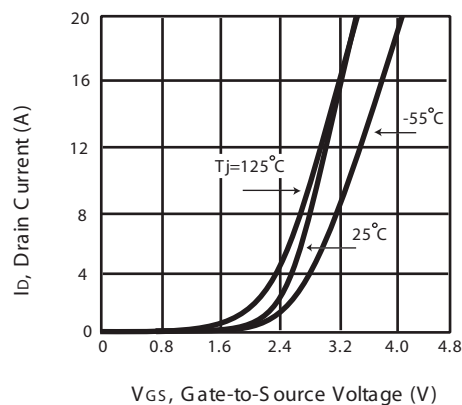


Figure 2. Transfer Characteristics

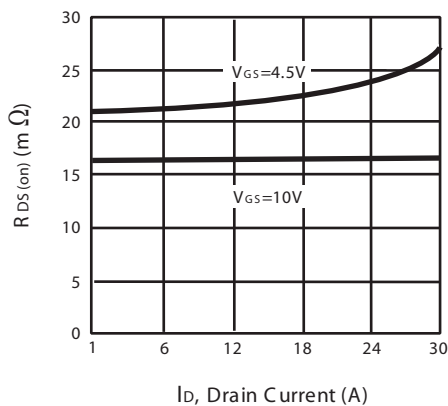


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

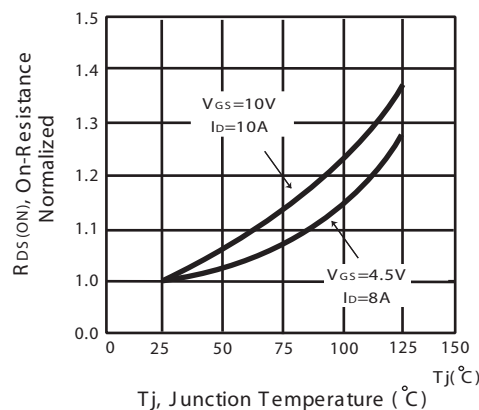


Figure 4. On-Resistance Variation with Drain Current and Temperature

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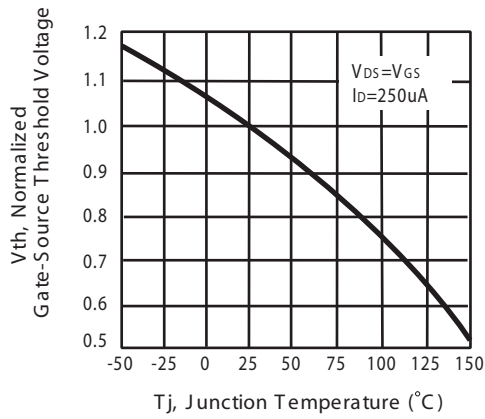


Figure 5. Gate Threshold Variation with Temperature

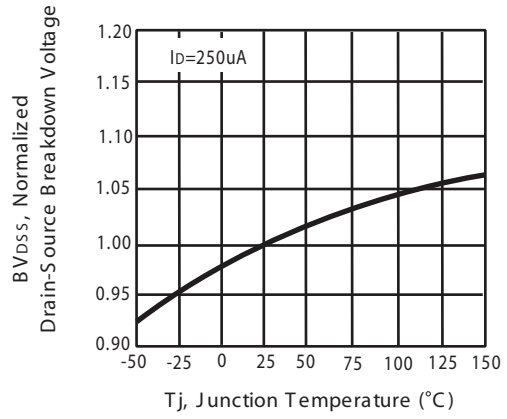


Figure 6. Breakdown Voltage Variation with Temperature

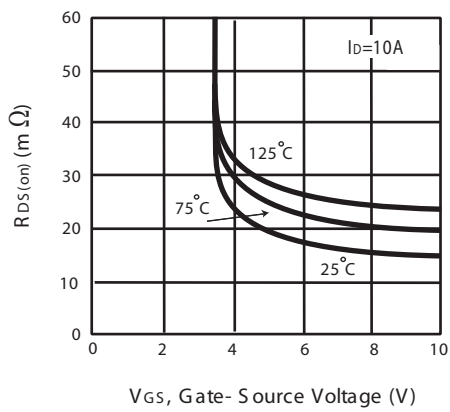


Figure 7. On-Resistance vs. Gate-Source Voltage

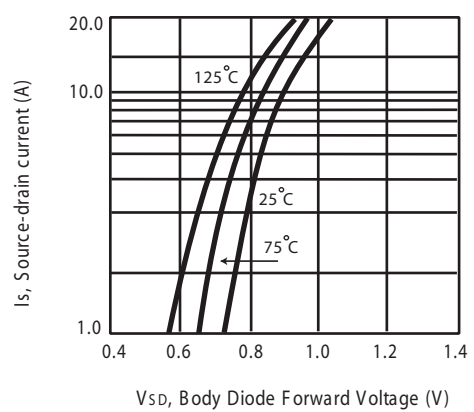


Figure 8. Body Diode Forward Voltage Variation with Source Current

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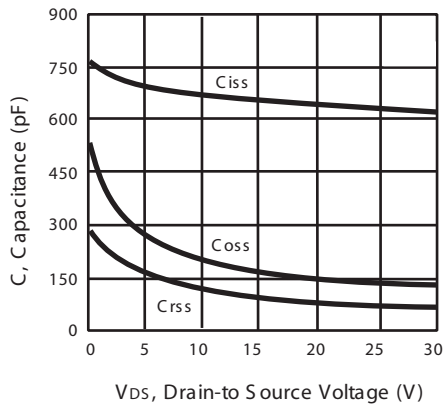


Figure 10. Capacitance

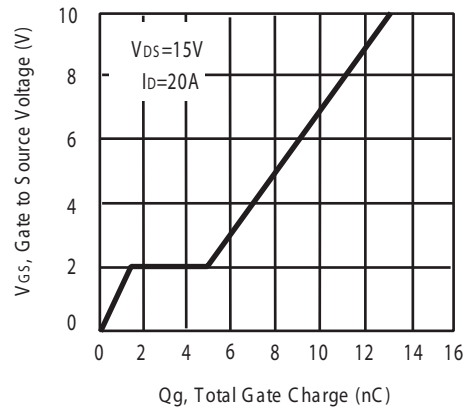


Figure 11. Gate Charge

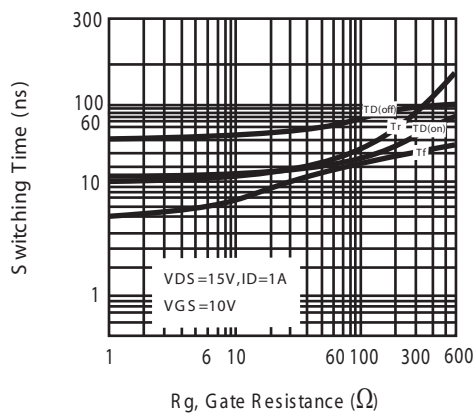


Figure 12. switching characteristics

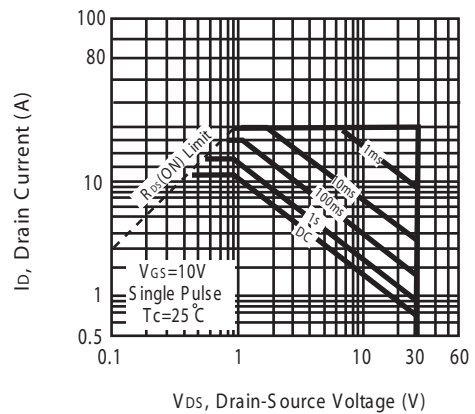


Figure 13. Maximum Safe Operating Area

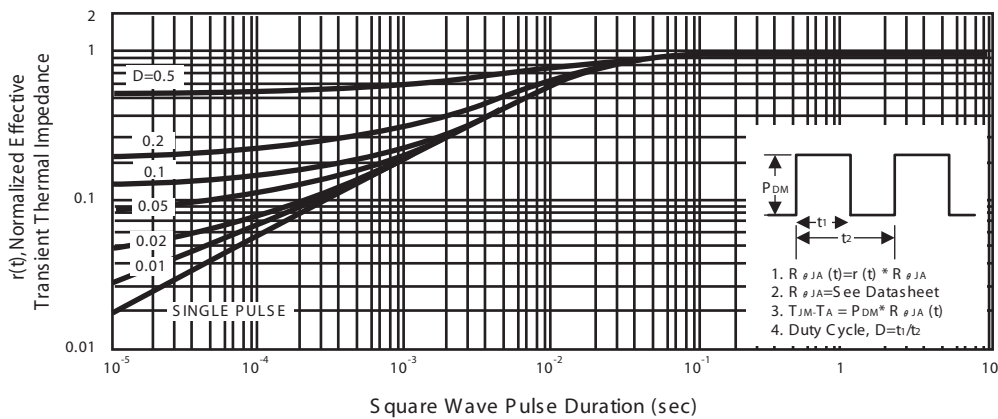


Figure 14. Normalized Thermal Transient Impedance Curve

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P-Channel

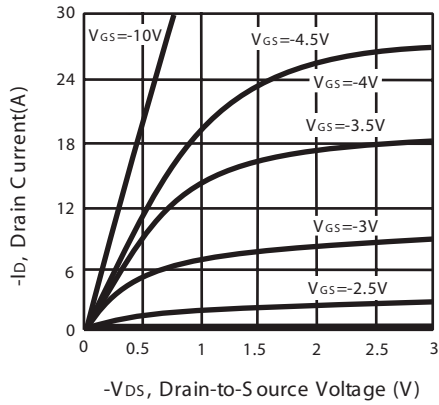


Figure 1. Output Characteristics

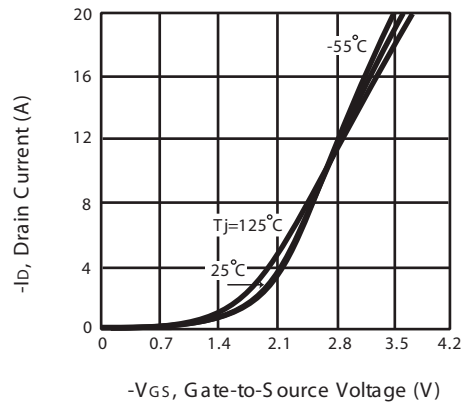


Figure 2. Transfer Characteristics

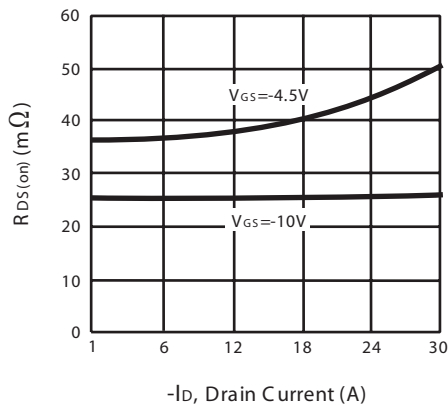


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

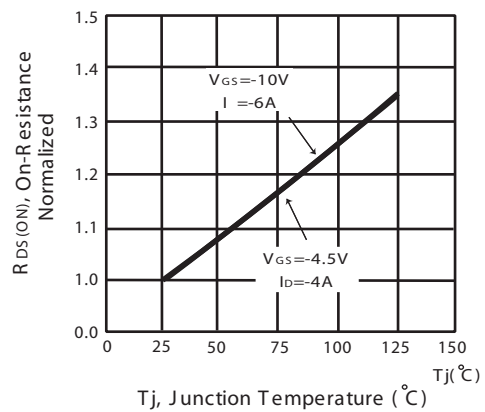


Figure 4. On-Resistance Variation with Drain Current and Temperature

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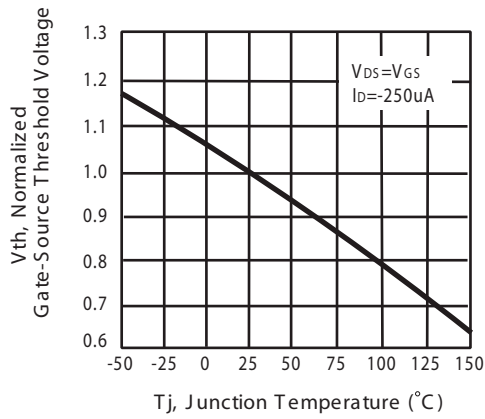


Figure 5. Gate Threshold Variation with Temperature

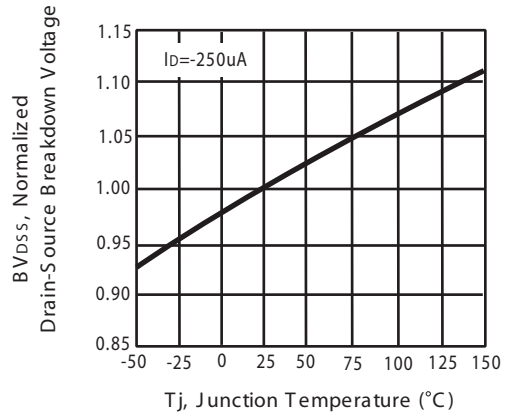


Figure 6. Breakdown Voltage Variation with Temperature

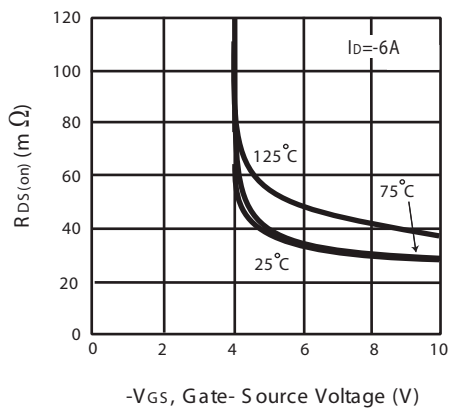


Figure 7. On-Resistance vs. Gate-Source Voltage

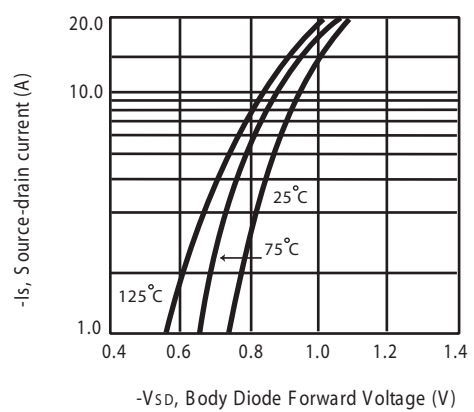


Figure 8. Body Diode Forward Voltage Variation with Source Current

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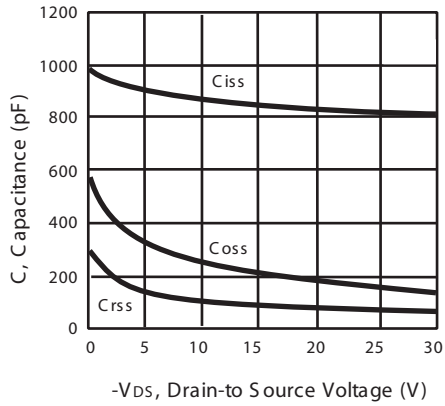


Figure 10. Capacitance

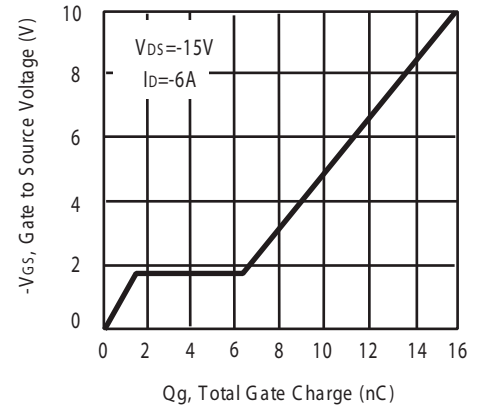


Figure 11. Gate Charge

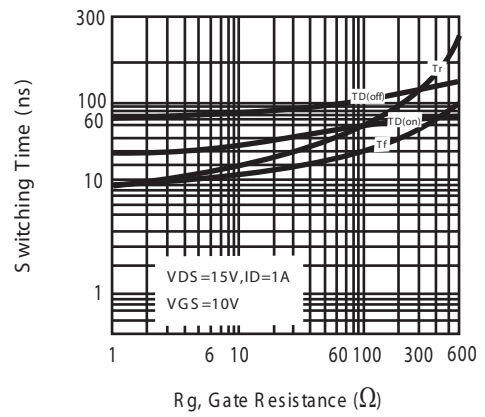


Figure 12. switching characteristics

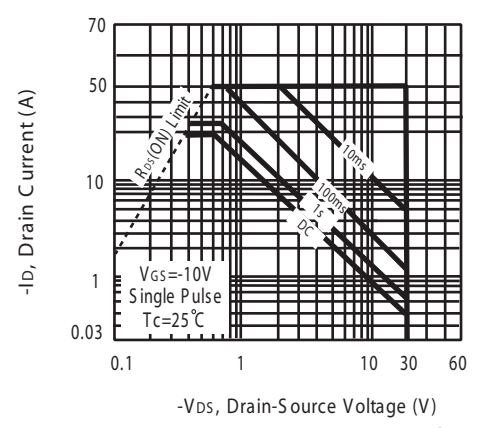


Figure 13. Maximum Safe Operating Area

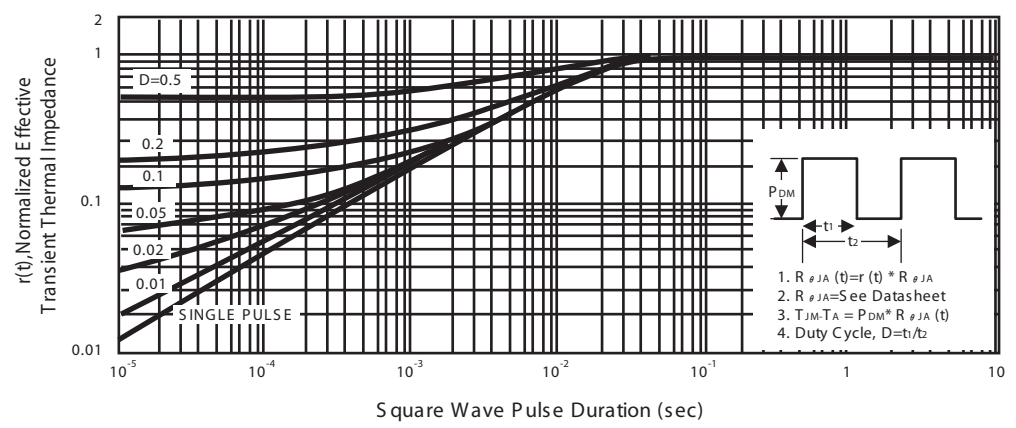
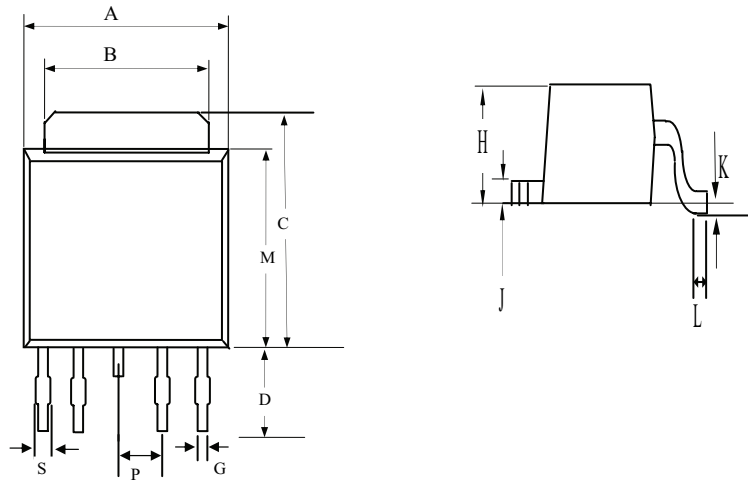


Figure 14. Normalized Thermal Transient Impedance Curve

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PACKAGE OUTLINE DIMENSIONS

TO-252-4L

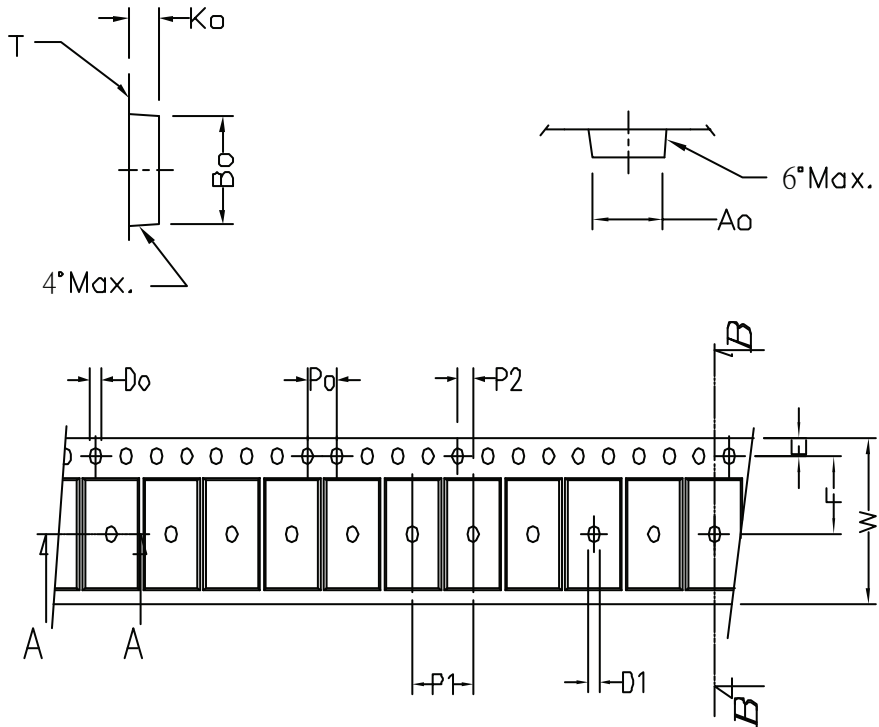


REF .	Millimeters	
	MIN	MAX
A	6.40	6.80
B	5.2	5.50
C	6.80	10.20
D	2.20	3.00
P	1.27 REF.	
S	0.50	0.80
G	0.40	0.60
H	2.20	2.40
J	0.45	0.60
K	0	0.15
L	0.90	1.50
M	5.40	5.80

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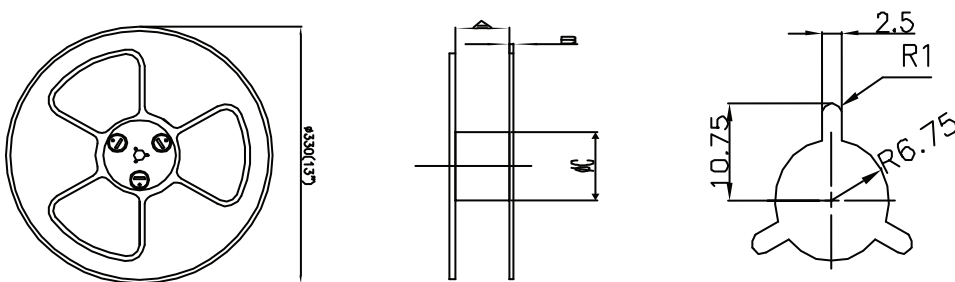
TO-252-4L Tape and Reel Data

TO-252-4L Carrier Tape



symbol	A_o	B_o	K_o	P_o	P_1	P_2	T
Spec	6.96 ± 0.1	10.49 ± 0.1	2.79 ± 0.1	4.0 ± 0.1	8.0 ± 0.10	2.0 ± 0.05	0.33 ± 0.013
symbol	E	F	D_o	D_1	W	$10P_o$	
Spec	1.75 ± 0.1	7.5 ± 0.05	1.55 ± 0.05	1.5 ± 0.25	16.0 ± 0.3 16.0 ± 0.1	40.0 ± 0.2	

TO-252-4L Reel



UNIT:mm

Width of carrier tape	8	12	16	24	32	44	56
$A \pm 0.1$	9.4	13.4	17.4	25.4	33.4	45.4	57.4
B	2.3	2.3	2.3	2.3	2.3	2.3	2.3
ϕC	100	100	100	100	100	100	100